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# **Analysis of a Faulted 4H Structure of CdI2**

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A faulted 4H structure of  $CdI_2$  gives a diffraction pattern composed of sharp spots and diffuse streaks. The structure was solved by assuming that the sharp spots come from the 'average structure' and the diffuse streaks from one-dimensional disorder.

### **Introduction**

Mitchell (1956) has reported that the most common polytype of  $CdI_2$  is type 4H with the ABC sequence  $(A\gamma B)(A\beta C)$  and the second common type is type 2H with  $(A \gamma B)$ . However, faulted  $4H$  structures appear more frequently than type  $2H$  in as-grown crystals (Minagawa, 1976). This paper describes the structure of a faulted 4H structure in terms of a stacking disorder of  $V$  and  $V'$ , where  $V$  and  $V'$  stand for the layer units  $(A\gamma B)$  and  $(A\beta C)$ , respectively.

#### **Experimental**

Crystals grown from aqueous solutions were hexagonal plates. All ten crystals examined revealed that one side of a crystal plate was of faulted 4H, while the other side was of type  $4H$  or  $2H$ . No single crystal of faulted 4H only was obtained. The crystal used for intensity measurement consisted of faulted 4H on one side and type  $2H$  on the other and had dimensions 570  $\mu$ m in width and 50  $\mu$ m in thickness. The domain of the faulted  $4H$  in the crystal was estimated to be 20  $\mu$ m thick by comparing the intensities of back and penetrating reflexions. Since the linear absorption coefficient,  $\mu$ , of CdI<sub>2</sub> is 1568 for Cu K $\alpha$ , 99.7% of the intensity of a back reflexion comes from a surface layer 20  $\mu$ m thick. Hence, the intensities of back reflexions may be considered to be given by the faulted 4H only.

With Cu  $K\alpha$  radiation, intensity data of sharp spots and diffuse streaks were recorded on zero-layer Weissenberg photographs about b. The characteristics of the sharp spots and the diffuse streaks from the faulted  $4H$  are as follows. (1) The positions of the sharp spots coincide with those of the corresponding spots for type 4H. The spot with  $\zeta = l$  has an intensity between those of the corresponding spots for types 4H and 2H and the intensity of the spot with  $\zeta = l + \frac{1}{2}$ is weaker than that for type  $4H$ , where the thickness of one layer unit is chosen as the c axial length. (2) The diffuse intensities along  $c^*$  are very strong at  $\zeta = l + \frac{1}{2}$ and very weak at  $\zeta = l$  and their distributions are almost the same for  $h0\zeta$  rows with  $h=3n\pm 1$  (*n* an integer).

The intensities of the sharp spots were estimated visually and corrected for Lorentz and polarization effects, spot size and absorption (see Appendix). The photometrically measured diffuse intensities were corrected for absorption, the polarization effect and the geometrical factor with the formula given by Takaki, Kato & Sakurai (1975).





### **Structure of the faulted 4H**

If the sharp spots found at  $\zeta = l$  and  $l + \frac{1}{2}$  are regarded as Bragg reflexions from the average structure, its period along c should be twice the thickness of one layer unit. A stacking mode of layer units in a faulted  $4\dot{H}$  structure with such an average structure is given in Table 1, where  $w_1, w_2$  are the respective probabilities of finding V:  $(A\gamma B)$  and V':  $(A\beta C)$  at the first site, and  $w'_1$ ,  $w'_2$  those for the second site. Therefore  $w_1$  +  $w_2 = 1$  and  $w_1 + w_2 = 1$ .  $\beta_1$ ,  $\beta_2$  are the respective probabilities of finding  $V$  at the second site after  $V$ ,  $V'$  at the first site, and so on. The layer form factors for  $V, V'$  are given by

$$
V = N_1 N_2 [f_1 + f_{\text{Cd}} \varepsilon^* \exp(i\pi\zeta/2) + f_1 \varepsilon \exp(i\pi\zeta)]
$$
  

$$
V' = N_1 N_2 [f_1 + f_{\text{Cd}} \varepsilon \exp(i\pi\zeta/2) + f_1 \varepsilon^* \exp(i\pi\zeta)].
$$

where  $N_1$  and  $N_2$  are the numbers of unit cells along **a**, **b**, respectively,  $f_I$  and  $f_{Cd}$  are the atomic scattering factors for the I and Cd ions, respectively, and  $\varepsilon =$  $\exp\left[2\pi i(h-k)/3\right]$ , the phase factor corresponding to the displacement  $A \rightarrow B$ . The structure factor for the Bragg reflexion from the average structure and the diffuse intensity  $I_D(\varphi)$  are given by [Takaki & Sakurai (1976), equations  $(5a)$  and  $(5b)$ ]

$$
F = F_1 + F_2 \exp(2\pi i \zeta),
$$

where  $F_1 = w_1 V + w_2 V'$  and  $F_2 = w_1' V + w_2' V'$ ;

$$
I_D(\varphi) = \frac{1}{2} N(w_1 w_2 + w_1 w_2) |V - V'|^2
$$
  
 
$$
\times [(1 - x^2)/(1 + x^2 - 2x \cos 2\varphi)](1 + U \cos \varphi),
$$

where

$$
|V - V'|^{2} = 3[f_{1}^{2} + f_{\text{Cd}}^{2} - 2f_{1}f_{\text{Cd}} \cos (\varphi/4)],
$$
  

$$
U = \frac{2[w_{1}w_{2}(\beta_{1} - \beta_{2}) + w_{1}'w_{2}'(\alpha_{1} - \alpha_{2})]}{[(w_{1}w_{2} + w_{1}w_{2})(1 + x)]},
$$

 $x=(\alpha_1-\alpha_2)$  ( $\beta_1-\beta_2$ ),  $\varphi=2\pi\zeta$  and N is the number of layer units [Takaki & Sakurai (1976), equations (39a) and (39b)]. The structure factors for hk $\zeta$  reflexions are listed in Table 2. The distribution of diffuse intensities is the same for hk $\zeta$  rows with  $h - k = 3n + 1$ .

Table 2. *Structure factors for hk( reflexions* 

h — k	3n	$3n \pm 1$	
$+ +$	1V	$(w_1 + w_1)V + (w_2 + w_2)V'$ $(w_1 - w_1)(V - V')$	

The values of  $w_i$  and  $w_i$  are given by solving the average structure. The values of  $\alpha_i$  and  $\beta_i$  are given by solving diffuse intensities; then only two parameters, say  $\alpha_2$  and  $\beta_2$ , are independent, since there are the relations  $w_1\beta_1+w_2\beta_2=w_1'$  and  $w_1\alpha_1+w_2\alpha_2=w_1$ .

The best agreement was obtained between the observed and calculated structure factors by putting  $w_1 = 0.90$ ,  $w_2 = 0.10$ ,  $w_1 = 0.28$ ,  $w_2 = 0.72$ ,  $B = 1.5$  for the I ion and  $B = 3.0$  for the Cd ion, where B is the isotropic temperature factor. Table 3 gives the observed and calculated structure factors. The R index  $(R = \Sigma ||F_o| - |F_c||/\Sigma|F_o|)$  is 0.12. As for the diffuse streaks, the best intensity agreement was obtained with

### Table 3. *Observed and calculated structure factors*

Observed reflexions marked with an asterisk have a geometry of incident and reflected beams different from that in Fig. 2, so that they were corrected with the corresponding formula for the absorption factor. This case is not common; and so the formula is not given here.





Fig. 1. Comparison of observed (dots) and calculated (full lines) diffuse intensities.

the values of  $w_i$ ,  $w'_i$  given above and the values  $\alpha_1 =$ 0.64,  $\alpha_2 = 1.00$ ,  $\beta_1 = 0.20$  and  $\beta_2 = 1.00$ . A comparison of observed and calculated intensities is shown in Fig. 1.

#### **Discussion**

In the above result the value of  $w_2$  is small. Suppose  $w_2=0$ ; then the case becomes that of a stacking disorder of two kinds of double layer units VV and  $V'V$  given in Table 4, where  $g_1$  and  $g_2$  are the probabilities of finding *V V* and *V'V* in the crystal respectively. The structure factors of the average structure for this model showed a good agreement  $(R=0.12)$ with the observed values by putting  $g_1 = 0.36$  and  $g_2 =$ 0-64. The diffuse intensities for this model are given by:

$$
I'_D(\varphi) = \frac{1}{2} N g_1 g_2 |V - V'|^2 [(1 - y^2)/(1 + y^2 - 2y \cos 2\varphi)],
$$

where  $y = \alpha - \beta$ .  $I'_p(\varphi)$  does not contain the factor  $1 + U \cos \varphi$  in  $I_D(\varphi)$  and  $U = -0.77$  for the present result, so that  $I_p(\varphi)$  gives quite different intensities from those observed. This suggests that the analysis of diffuse intensities is an important key in justifying a model for the faulted structure.

Table 4. *Stacking mode of two kinds of double layer units* 

	vν	V'V
VV $\frac{g_1}{g_2}$ V'V	α	$1-\alpha$

It is interesting that in the present result the relations  $w_1(1-\beta_1) = w_2\alpha_2$  and  $w_2\beta_2 = w_1(1-\alpha_1)$  are satisfied, *i.e.* the number of the pair *V V'* is equal to that of *V'V.* These relations have also been found in a disordered structure of o-chlorobenzamide (Takaki, Kato & Sakurai, 1975).

In other crystal samples with faulted 4H structures, the intensity distributions of sharp spots and diffuse streaks vary from crystal to crystal. They could also be explained in terms of the stacking mode of layer units given in Table 1.

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## APPENDIX

## **Absorption factor for back reflexions from a disc-shaped crystal**

Let us calculate the absorption factor for zero-layer back reflexions from a disc-shaped crystal when the crystal is rotated about an axis parallel to a diameter and which passes through the centre of the disc. Fig. 2 shows a cross-section perpendicular to the rotation axis, together with the geometry of the incident and reflected beams for the reflexions given in Table 3 (two extreme cases are  $\gamma=81.3$ ,  $\delta=8.0^{\circ}$  for 205 and  $\gamma = 8.0, \delta = 81.3^{\circ}$  for 205). The absorption factor A for the disc is obtained by using the formula for the ab-



Fig. 2. A cross-section of a disc-shaped crystal perpendicular to the rotation axis, illustrating the geometry of the incident and reflected beams.

sorption factor of a right-prismatic crystal given by Takaki, Sakata & Watanabé (1961) and by assuming that the diameter  $r$  is fairly large compared with the thickness  $b (b/r = 1/11.4$  in the present case):

$$
A = (4/\pi r b \mu^2) (A_1 + A_2 + A_3),
$$

where  $\mu$  is the linear absorption coefficient.

$$
A_1 = (\csc \gamma + \csc \delta)^{-1} [(\mu \pi r/4) (1 - C_1 C_2)
$$
  
+  $\mu b(\cot \gamma + \cot \delta) C_1 C_2$   
- (1 - C\_1 C\_2) (\cot \gamma + \cot \delta)/(\csc \gamma + \csc \delta)],  
A\_2 = \cos \gamma [\sin \delta (1 - C\_2)

$$
-(1-C_1C_2)/(\csc \gamma + \csc \delta)],
$$

$$
A_3 = \cos \delta[\sin \gamma (1 - C_1) - (1 - C_1 C_2)/(\csc \gamma + \csc \delta)],
$$

$$
C_1 = \exp(-\mu b \csc \gamma),
$$

$$
C_2 = \exp(-\mu b \csc \delta)
$$

and  $\gamma$  and  $\delta$  are the angles given in Fig. 2.

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